

G1  
I'   
concl

a second single crystal substrate portion having active devices formed thereon and defining a device surface wherein the dielectric layer of the first substrate portion is bonded to the device surface of the second substrate portion, wherein selected ones of said active devices of said second substrate portion are intercoupled via metal lines.

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G2  
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31. (Amended) An apparatus comprising:  
a primary substrate having a first level of devices formed thereon and defining a device surface; and  
at least one secondary single crystal substrate coupled to the device surface, the at least one secondary substrate having active devices formed thereon and selected ones of said active devices of said at least one secondary single crystal substrate are intercoupled via metal lines.

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Please add the following new claims:

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G3

--33. (New) The apparatus of claim 28, wherein said first substrate portion is made of a single crystal silicon.

34. (New) The apparatus of claim 31, wherein said primary substrate is made of a single crystal silicon.--

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